

## CLAIMS

1-12. (Canceled)

13. (Currently amended) A method of fabricating a dielectric material, said method comprising: incorporating a Group V element in a Group III metal oxide, wherein said dielectric material is deposited in an atmosphere comprising a mixture of oxygen and nitrogen.

14. (Original) A method according to claim 13, wherein said Group III metal oxide is aluminum oxide.

15. (Original) A method according to claim 13, wherein said Group V element is selected from the group consisting of nitrogen and phosphorous.

16. (Original) A method according to claim 14, wherein said Group V element is selected from the group consisting of nitrogen and phosphorous.

17. (Canceled)

18. (Currently amended) A method according to claim 13 [[17]], wherein said mixture of oxygen and nitrogen has an oxygen-to-nitrogen ratio ranging from about 24:6 to about 9:21.

19. (Currently amended) A method according to claim 13 [[17]], wherein said mixture of oxygen and nitrogen has an oxygen-to-nitrogen ratio of about 18:12.

20. (Canceled)

21. (Original) A method according to claim 13, wherein said dielectric material is formed by a technique selected from the group consisting of reactive sputtering, annealing, atomic layer deposition (ALD), chemical vapor deposition (CVD), metalorganic chemical vapor deposition (MOCVD), plasma nitridation, and oxidation of metal nitrides.

22-26. (Canceled)

27. (New) A method according to claim 13, comprising forming the dielectric material on a substrate using the oxygen and the nitrogen from said atmosphere.

28. (New) A method according to claim 16, wherein:  
said mixture of oxygen and nitrogen has an oxygen-to-nitrogen ratio ranging from about 24:6 to about 9:21;  
said dielectric material is formed by a technique selected from the group consisting of reactive sputtering, annealing, atomic layer deposition (ALD), chemical vapor deposition (CVD), metalorganic chemical vapor deposition (MOCVD), plasma nitridation, and oxidation of metal nitrides; and  
the method comprises the step of forming the dielectric material on a substrate using the oxygen and the nitrogen from said atmosphere.

29. (New) A method according to claim 28, wherein said mixture of oxygen and nitrogen has an oxygen-to-nitrogen ratio of about 18:12.

30. (New) A method of fabricating a dielectric material, said method comprising: incorporating a Group V element in a Group III metal oxide, wherein said Group V element is phosphorous.

31. (New) A method according to claim 30, wherein said Group III metal oxide is aluminum oxide.